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**(71) Applicant(s):**

REC SCANWAFER AS [NO/NO]; Tormod Gjestlands vei 41 N-3908 Porsgrunn (NO) *(for all designated states except US)*  
ULSET, Torgeir [NO/NO]; Peder Claussonsgt. 2 N-4630 Kristiansand (NO) *(for US only)*  
JULSRUD, Stein [NO/NO]; Gregorius Dagssonsgt. 190 N-3713 Skien (NO) *(for US only)*  
CASSAYRE, Laurent [FR/FR]; 10 rue Briqueterie F-31400 Toulouse (FR) *(for US only)*  
CHAMELOT, Pierre [FR/FR]; 16 rue Montségur F-31120 Lacroix-Falgarde (FR) *(for US only)*  
MASSOT, Laurent [FR/FR]; 6 Clos de Montplaisir F-31460 Caraman (FR) *(for US only)*  
TAXIL, Pierre [FR/FR]; 10 rue Paul Codos F-31400 Toulouse (FR) *(for US only)*  
NAAS, Tyke, Laurence [NO/NO]; Tårnfjellvn. 33 N-3910 Porsgrunn (NO) *(for US only)*

**(72) Inventor(s):**

ULSET, Torgeir; Peder Claussonsgt. 2 N-4630 Kristiansand (NO)  
JULSRUD, Stein; Gregorius Dagssonsgt. 190 N-3713 Skien (NO)  
CASSAYRE, Laurent; 10 rue Briqueterie F-31400 Toulouse (FR)  
CHAMELOT, Pierre; 16 rue Montségur F-31120 Lacroix-Falgarde (FR)  
MASSOT, Laurent; 6 Clos de Montplaisir F-31460 Caraman (FR)  
TAXIL, Pierre; 10 rue Paul Codos F-31400 Toulouse (FR)  
NAAS, Tyke, Laurence; Tårnfjellvn. 33 N-3910 Porsgrunn (NO)

**(74) Agent(s):**

ONSAGERS AS; P.O.Box 6963 St. Olavs plass N-0130 Oslo (NO)

**(54) Title (EN):** METHOD FOR RECOVERING ELEMENTAL SILICON FROM CUTTING REMAINS

**(54) Title (FR):** PROCÉDÉ DE RÉCUPÉRATION DE SILICIUM ÉLÉMENTAIRE À PARTIR DE DÉBRIS DE DÉCOUPE

**(57) Abstract:**

**(EN):** This invention relates to a method for recovering elemental silicon cutting remains containing silicon particles, wherein the method comprises manufacturing solid anodes from the cutting remains, arranging one or more manufactured anode (s) in an electrolytic cell with a molten salt electrolyte and one or more cathode (s), and applying a potential difference between the one or more anode (s) and cathode (s) to obtain an oxidation of metallic silicon in the one or more anode (s), transportation of dissolved silicon in the electrolyte, and reduction of the dissolved silicon to a metallic phase at the one or more cathode (s).

**(FR):** Cette invention porte sur un procédé de récupération de débris de découpe de silicium élémentaire contenant des particules de silicium. Le procédé comprend la fabrication d'anodes solides à partir des débris de découpe, l'arrangement d'une ou plusieurs anodes fabriquées dans une cellule électrolytique avec un électrolyte et une ou plusieurs cathodes, et l'application d'une différence de potentiel entre une ou plusieurs anodes et une ou plusieurs cathodes afin d'obtenir une oxydation de silicium métallique

dans une ou plusieurs anodes, le transport de silicium dissous dans l'électrolyte, et la réduction du silicium dissous à une phase métallique au niveau d'une ou plusieurs cathodes.

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